Amendments to the Specification:

Please replace the paragraph beginning at page 5, line 14 with the following replacement paragraph:

In order to overcome these defects, there has been proposed the film formation of a high-K material by using plasma CVD (see, Byeong-Ok Cho, Sandy Lao, Lin Sha and Jane P. Chang, Journal of Vacuum Science and Technology, A19(6), pp. 2751-2761 (Nov/Dec 2001); Benjamin Chin-ming Lai, Nan-hui Kung and Ya-min Lee, Journal of Applied Physics, Vol. 85, No. 8, pp. 4087-4090 (April 15, 1999); Hiromitsu Kato, Tomohiro Nango, Takeshi Miyagawa, Takahiro Katagiri, Yoshimitsu Ohki, Kwang Soo Seol and Makoto Takyama, 2001 Dry Process International Symposium Proceeding, pp. 175-180; Gerald Lucovsky, Hiro Niimi, Robert ~~Jhonson~~ Johnson, Joon Goo Hong, Robert Therrien and Bruce Rayner, SSDM 2000, Abstracts, pp. 232-233). In the plasma process, the film can be formed at a substrate temperature up to about 400°C, and in this temperature region, a large amount of reactive oxygen species can be produced, so that a high-dielectric constant material having a low carbon concentration can be produced at a low temperature (see, the above-mentioned paper by Byeong-Ok Cho et al.).

Please replace the paragraph beginning at page 10, line 12 with the following replacement paragraph:

The electronic device substrate which can be used in the present invention is not particularly limited, but may be a substrate (or base material) which is appropriately selected from any one of known electronic device substrates, or a combination of two or more kinds thereof. Specific Examples of the electronic device substrate may include: semiconductor materials and liquid crystal device materials. Examples of the semiconductor material may include materials mainly comprising a single-crystal ~~silicone~~ silicon, and examples of the liquid crystal device material may include a glass substrate.

Please replace the paragraph beginning at page 10, line 30 with the following replacement paragraph:

The film forming substance which can be used in the present invention is not particularly limited, as long as it is a substance capable of providing a film or layer on the above-mentioned electronic device substrate on the basis of a vapor deposition process. In view of recent requirements (e.g., finer structure, larger-area film process, lower-temperature treatment) on the market, for example, a film-forming substance for gate insulator and/or a film-forming substance for interlayer insulating film can particularly suitably [[e]] be used as the film-forming substance.

Please replace the paragraph beginning at page 14, line 29 with the following replacement paragraph:

First, as an example of the structure of a semiconductor device which can be produced by the process for producing an electronic device material according to the present invention, a semiconductor device having an MOS structure having a gate insulator as the insulating film is described below with reference to Fig. [[2]]1.

Please replace the paragraph beginning at page 15, line 12 with the following replacement paragraph:

In this example, it is preferred that the high-quality oxide film 21 comprises a ~~silicone~~ silicon oxide film (hereinafter referred to as "SiO_2 film") which has been formed by irradiating a substrate to be treated mainly comprising Si, with a microwave through a plane antenna member having a plurality of slots in the presence of a process gas comprising O_2 and a rare gas so as to generate plasma, and forming the oxide film on the surface of the substrate by using the thus generated plasma. When such SiO_2 is used, the structure of the apparatus to be used therefor is the same as that of the apparatus for forming an insulating film. As a result, it is possible to obtain an advantage that the film can be formed in the same chamber, or operationality can be improved, or the space for the apparatus (foot-print) can be saved, because of the same specification between these apparatuses.

Please replace the paragraph beginning at page 15, line 29 with the following replacement paragraph:

In the present invention, in view of the reduction effect in the electrical film thickness, the surface of the silicon oxide film 21 may preferably be subjected to a nitridation treatment by introducing a nitrogen gas into the above-mentioned plasma. Alternatively, instead of the silicon oxide film 21, it is also possible to use a plasma nitride film which has been formed by introducing a nitrogen gas directly into the plasma on the Si substrate. On the silicon oxide film, oxynitride film or nitride film, a gate insulator 22 is formed by using the process according to present invention, and further, a gate ~~insulator~~ electrode 13 mainly comprising silicon (polysilicon or amorphous silicon) is formed. The gate insulator 22 according to the present invention may also be formed directly on the Si substrate.